2N5152, 2N5152L, 2N5154, 2N5154L



NPN Power Silicon Transistor

Rev. V3

Features

- Available in commercial, JAN, JANTX, JANTXV, JANS and JANSR 100K rads (Si) per MIL-PRF-19500/544
- TO-5 Package: 2N5151L, 2N5153L
 TO-39 Package: 2N5151, 2N5153
- Ideal for High Current Switching Applications



Electrical Characteristics (T_A = +25°C unless otherwise specified)

Parameter	Test Conditions	Symbol	Units	Min.	Max.
Collector - Emitter Breakdown Voltage	$I_{\rm C}$ = 100 mA dc, $I_{\rm B}$ = 0	$V_{(BR)CEO}$	V dc	80	_
Emitter - Base Cutoff Current			μΑ dc mA dc	_	1.0 1.0
Collector - Emitter Cutoff Current	$V_{CE} = 60 \text{ V dc}, V_{BE} = 0$ $V_{CE} = 100 \text{ V dc}, V_{BE} = 0$	I _{CES1}	μA dc mA dc	_	1.0 1.0
Collector - Emitter Cutoff Current	$V_{CE} = 40 \text{ Vdc}, I_B = 0$	I _{CEO}	μA dc	_	50
Forward Current Transfer Ratio	I_C = 50 mA dc, V_{CE} = 5.0 Vdc 2N5152, 2N5152L 2N5154, 2N5154L I_C = 2.5 A dc, V_{CE} = 5.0 Vdc 2N5152, 2N5152L	52, 2N5152L h _{FE1} 54, 2N5154L dc, V _{CE} = 5.0 Vdc 52, 2N5152L h _{FE2}		20 50 30 70	90 200
	$2N5154$, $2N5154L$ $I_C = 5.0 \text{ A dc}$, $V_{CE} = 5.0 \text{ Vdc}$ $2N5152$, $2N5152L$ $2N5154$, $2N5154L$	h _{FE3}		20 40	
Collector - Emitter Saturation Voltage	I_{C} = 2.5 Adc, I_{B} = 250 mAdc V_{CI} I_{C} = 5.0 Adc, I_{B} = 500 mAdc V_{CI}			_	0.75 1.50
Base - Emitter Voltage (nonsaturated)	$I_C = 2.5 \text{ A dc}, V_{CE} = 5.0 \text{ Vdc}$	V _{BE}	V dc	_	1.45
Emitter - Base Saturation Voltage	I_C = 2.5 A dc, I_B = 250 mA dc I_C = 5.0 A dc, I_B = 500 mA dc	V _{BE(SAT)1}		_	1.45 2.20
Collector-Emitter Cutoff Current	T_{C} = +150°C V_{CE} = 60 V dc, V_{BE} = -2 V dc	I _{CEX}	μA dc	<u>—</u>	25
Forward-Current Transfer Ratio	$T_C = -55^{\circ}C$ $V_{CE} = 5 \text{ V dc}, I_C = 2.5 \text{ A dc}$ $2N5152, 2N5152L$ $2N5154, 2N5154L$	h _{FE4}		15 25	

(Continued next page)

2N5152, 2N5152L, 2N5154, 2N5154L



NPN Power Silicon Transistor

Rev. V3

Electrical Characteristics (T_A = +25°C unless otherwise specified)

Parameter	Test Conditions	Symbol	Units	Min.	Max.		
Dynamic Characteristics							
Magnitude of Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio	I_C = 500 mA dc, V_{CE} = 5.0 Vdc, f = 10 MHz 2N5152, 2N5152L 2N5154, 2N5154L		-	6 7	_		
Common-Emitter, Small-Signal, Short-Circuit, Forward-Current Transfer Ratio	I _C = 100 mA dc, V _{CE} = 5.0 Vdc, f = 1 kHz 2N5152, 2N5152L 2N5154, 2N5154L		-	20 50	_		
Open-Circuit Output Capacitance	$V_{CB} = 10 \text{ Vdc}, I_E = 0, f = 1 \text{ MHz}$		pF	_	250		
Parameter	rameter Test Conditions		Units	Min.	Max.		
Switching Characteristics							
Turn-On Time		t_{on}	μs	_	0.5		
Storage Time	I_{C} = 5 A dc; I_{B1} = 500 mA dc, R_{L} = 6 Ω ,	ts	μs	_	1.4		
Fall Time	I_{B2} = -500 mA dc, $V_{BE(off)}$ = 3.7 Vdc	t _f	μs	_	0.5		
Turn-Off Time		t_{off}	μs	_	1.5		

Safe Operating Area

DC Tests: $T_C = +25^{\circ}C$, I Cycle, $t_p = 1$ s

Test 1: $V_{CE} = 5 \text{ V dc}, I_{C} = 2 \text{ A dc}$

Test 2: $V_{CE} = 32 \text{ V dc}, I_{C} = 310 \text{ mA dc}$

Test 3: $V_{CE} = 80 \text{ V dc}, I_{C} = 12.5 \text{ mA dc}$

(Unclamped inductive) $T_C = +25^{\circ}C$, $R_{BB1} = 10\Omega$

$$\begin{split} R_{BB2} &= 100\Omega,\, L = 0.3 \text{ mH} \\ RL &= 0.1\Omega,\, V_{CC} = 10 \text{ V dc} \\ V_{BB1} &= 10 \text{ V dc},\, V_{BB2} = 4 \text{ V dc} \end{split}$$

 I_{CM} = 10 A dc (see figure 15 of MIL-PRF-19500/544)

2N5152, 2N5152L, 2N5154, 2N5154L



NPN Power Silicon Transistor

Rev. V3

Absolute Maximum Ratings (T_A = +25°C unless otherwise specified)

Ratings	Symbol	Value
Collector - Emitter Voltage	V _{CEO}	80 V dc
Collector - Base Voltage	V _{CBO}	100 V dc
Emitter - Base Voltage	V _{EBO}	5.5 V dc
Collector Current	I _C	2 A dc 10 A dc ⁽¹⁾
Total Power Dissipation @ T _A = 25°C @ T _C = 25°C	P _T	1 W 10 W
Reverse Pulse Energy (2)		15 mJ
Operating & Storage Temperature Range	T _J , T _{stg}	-65°C to +200°C

Thermal Characteristics

Characteristics	Symbol	Max. Value
Thermal Resistance, Junction to Case (4)	$R_{ heta JC}$	10°C/W
Thermal Resistance, Junction to Ambient ⁽⁴⁾	$R_{\theta JA}$	175°C/W

- 1. This value applies for PW ≤ 8.3 ms, duty cycle ≤ 1%.
- 2. This rating is based on the capability of the transistors to operate safely in the unclamped inductive load energy test circuit.
- 3. For thermal impedance curves see figures 10, 11, and 12 of MIL-PRF-19500/544
- 4. For thermal impedance curves, see figures 10, 11, and 12 of MIL-PRF-19500/544

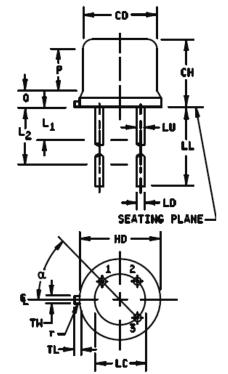


NPN Power Silicon Transistor

Rev. V3

Outline Drawings (TO-5, TO-39)

	Dimensions					
Symbol	Inches Millimeters		neters	Note		
	Min	Max	Min	Max		
CD	.305	.335	7.75	8.51	6	
CH	.240	.260	6.10	6.60		
HD	.335	.370	8.51	9.40		
LC	.200	TP	5.08 TP		7	
LD	.016	.019	0.41	0.48	8,9	
LL	See note 14					
LU	.016	.019	0.41	0.48	8,9	
L ₁		.050		1.27	8,9	
L ₂	.250		6.35		8,9	
Р	.100		2.54		7	
Q		.030		0.76	5	
TL	.029	.045	0.74	1.14	3,4	
TW	.028	.034	0.71	0.86	3	
r		.010		0.25	10	
α	45°	TP	45° TP		7	
1, 2, 10, 12, 13, 14						



NOTES:

- Dimensions are in inches.
- 2. Millimeters are given for general information only.
- Beyond r (radius) maximum, TW shall be held for a minimum length of .011 (0.28 mm).
- Dimension TL measured from maximum HD.
- Body contour optional within zone defined by HD, CD, and Q.
- 6. CD shall not vary more than .010 inch (0.25 mm) in zone P. This zone is controlled for automatic handling.
- Leads at gauge plane .054 +.001 -.000 inch (1.37 +0.03 -0.00 mm) below seating plane shall be within .007 inch (0.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC. The device may be measured by direct methods or by gauging procedure.
- Dimension LU applies between L₁ and L₂. Dimension LD applies between L₂ and LL minimum. Diameter is uncontrolled in and beyond LL minimum.
- 9. All three leads.
- 10. The collector shall be internally connected to the case.
- Dimension r (radius) applies to both inside comers of tab.
- 12. In accordance with ASME Y14.5M, diameters are equivalent to Φx symbology.
- Lead 1 = emitter, lead 2 = base, lead 3 = collector.
- For L-suffix devices (TO-5), dimension LL = 1.5 inches (38.10 mm) min. and 1.75 inches (44.45 mm) max. For no suffix types (TO-39), dimension LL = .5 inch (12.70 mm) min. and .750 inch (19.05 mm) max.

FIGURE 1. Physical dimensions (similar to TO-5 and TO-39).

2N5152, 2N5152L,2N5154, 2N5154L



NPN Power Silicon Transistor

Rev. V3

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